TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

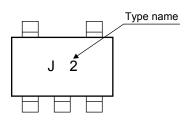
# TC7SZ08F,TC7SZ08FU

#### 2-Input AND Gate

#### Features

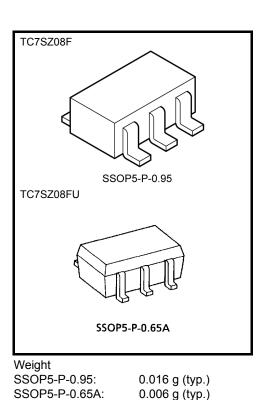
- High output drive: ±24 mA (min) at V<sub>CC</sub> = 3 V
- Super high speed operation: t<sub>pd</sub> = 2.7 ns (typ.) at V<sub>CC</sub> = 5 V, 50 pF
- Operation voltage range: V<sub>CC (opr)</sub> = 1.8 to 5.5 V
- 5.5-V tolerant inputs
- 5.5-V power down protection output
- Matches the performance of TC74LCX series when operated at 3.3-V  $V_{CC}$

## Marking

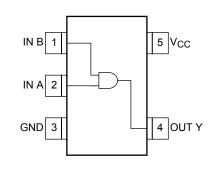


## Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V <sub>CC</sub>	–0.5 to 6	V	
DC input voltage	V <sub>IN</sub>	–0.5 to 6	V	
DC output voltage	Vour	-0.5 to 6 (Note 1)	V	
DC output voltage	Vout	-0.5 to VCC+0.5 (Note 2)	v	
Input diode current	I <sub>IK</sub>	-20	mA	
Output diode current	IOK	-20 (Note 3)	mA	
DC output current	lout	±50	mA	
DC V <sub>CC</sub> /ground current	ICC	±50	mA	
Power dissipation	PD	200	mW	
Storage temperature	T <sub>stg</sub>	–65 to 150	°C	
Lead temperature (10 s)	ΤL	260	°C	



#### Pin Assignment (top view)



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: 
$$V_{CC} = 0 V$$

Note 2: High or Low State. I<sub>OUT</sub> absolute maximum rating must be observed.

Note 3: V<sub>OUT</sub> < GND

# <u>TOSHIBA</u>

# Logic Diagram



# Truth Table

Inp	out	Output				
А	В	Y				
L	L	L				
L	Н	L				
Н	L	L				
Н	Н	Н				

# **Operating Ranges**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	1.8 to 5.5	V
Supply vollage		1.5 to 5.5 (Note 4)	v
Input voltage	V <sub>IN</sub>	0 to 5.5	V
Output voltage	Vout	0 to 5.5 (Note 5)	V
		0 to V <sub>CC</sub> (Note 6)	v
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
	dt/dv	0 to 20 (V_{CC} = 1.8 V, 2.5 V $\pm$ 0.2 V)	ns/V
Input rise and fall time		0 to 10 (V_{CC} = 3.3 V $\pm$ 0.3 V)	
		0 to 5 (V_{CC} = 5.0 V $\pm$ 0.5 V)	

Note 4: Data retention only

Note 5:  $V_{CC} = 0 V$ 

Note 6: High or Low state

# **Electrical Characteristics**

#### **DC Characteristics**

Characteristics	Symbol Test		Condition		Ta = 25°C		$Ta = -40$ to $85^{\circ}C$		Unit	
		Test Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
High-level VIH				1.8	V <sub>CC</sub> × 0.88	_	_	V <sub>CC</sub> × 0.88	_	
input voltage	VIH	VIH —		2.3 to 5.5	V <sub>CC</sub> × 0.75	_	_	V <sub>CC</sub> × 0.75	_	v
Low-level	Mu			1.8	_		V <sub>CC</sub> × 0.12	_	V <sub>CC</sub> × 0.12	
input voltage	VIL		—	2.3 to 5.5	_	_	V <sub>CC</sub> × 0.25	_	V <sub>CC</sub> × 0.25	
				1.8	1.7	1.8	_	1.7	_	-
			lou - 100 uA	2.3	2.2	2.3	_	2.2	—	
High-level output voltage	V <sub>OH</sub> V <sub>IN</sub>		I <sub>OH</sub> = −100 μA	3.0	2.9	3.0	_	2.9	—	
		V <sub>IN</sub> = V <sub>IH</sub>		4.5	4.4	4.5	_	4.4	—	
		VIN – VIH	I <sub>OH</sub> = -8 mA	2.3	1.9	2.15		1.9	—	
			I <sub>OH</sub> = -16 mA	3.0	2.4	2.8		2.4	_	
			I <sub>OH</sub> = -24 mA	3.0	2.3	2.68		2.3		
			I <sub>OH</sub> = -32 mA	4.5	3.8	4.2		3.8		v
	V <sub>OL</sub> V <sub>IN</sub> = V <sub>IH c</sub>	V <sub>IN</sub> = V <sub>IH or</sub> V <sub>IL</sub>	I <sub>OL</sub> = 100 μΑ	1.8		0	0.1		0.1	
				2.3	—	0	0.1		0.1	
				3.0	—	0	0.1		0.1	
Low-level output voltage				4.5		0	0.1		0.1	
			I <sub>OL</sub> = 8 mA	2.3		0.1	0.3		0.3	
			I <sub>OL</sub> = 16 mA	3.0		0.15	0.4		0.4	
		ŀ	I <sub>OL</sub> = 24 mA	3.0		0.22	0.55		0.55	
			I <sub>OL</sub> = 32 mA	4.5		0.22	0.55		0.55	
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0 to 5.5	_		±1		±10	μA
Power off leakage current	IOFF	$V_{IN}$ or $V_{OUT} = 5.5 V$		0.0	_		1		10	μA
Quiescent supply current	Icc	$V_{IN} = V_{CC}$ or GND		5.5	—		2	_	20	μA

### AC Characteristics (unless otherwise specified, Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = –40 to 85°C		Unit	
			V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	
Propagation delay time	<sup>t</sup> pLH t <sub>pHL</sub>	$C_L = 15 \text{ pF}, R_L = 1 \text{ M}\Omega$	1.8	2.0	5.2	10.0	2.0	10.5	- ns
			$2.5\pm0.2$	0.8	3.4	7.0	0.8	7.5	
			$\textbf{3.3}\pm\textbf{0.3}$	0.5	2.6	4.7	0.5	5.0	
			$5.0\pm0.5$	0.5	2.2	4.1	0.5	4.4	
		$C_L = 50 \text{ pF}, \text{ R}_L = 500 \Omega$	$\textbf{3.3}\pm\textbf{0.3}$	1.5	3.3	5.2	1.5	5.5	
			$5.0\pm0.5$	0.8	2.7	4.5	0.8	4.8	
Input capacitance	C <sub>IN</sub>	—	0 to 5.5	_	4	_	_	_	pF
Power dissipation capacitance	C <sub>PD</sub> (Not	(Note 7)	3.3	_	20	_	_	_	рF
		(Note 7)	5.5		25				Ы

Note 7: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

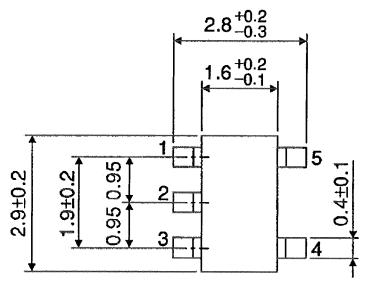
 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

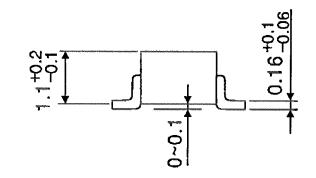
# <u>TOSHIBA</u>

# Package Dimensions

SSOP5-P-0.95

Unit : mm





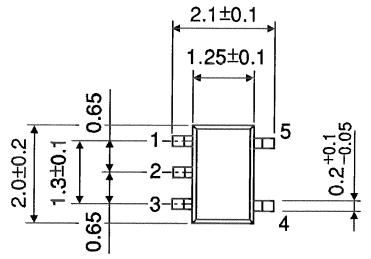
Weight: 0.016 g (typ.)

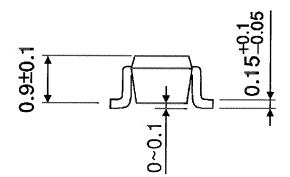


Package Dimensions

SSOP5-P-0.65A

Unit : mm





Weight: 0.006 g (typ.)

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20070701-EN GENERAL

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